

Title (en)

APPARATUS FOR PRODUCING SILICON CARBIDE SINGLE CRYSTAL AND METHOD FOR PRODUCING SILICON CARBIDE SINGLE CRYSTAL

Title (de)

VORRICHTUNG ZUR HERSTELLUNG EINES SILICIUMCARBID-EINZELKRISTALLS SOWIE VERFAHREN ZUR HERSTELLUNG EINES SILICIUMCARBID-EINZELKRISTALLS

Title (fr)

APPAREIL ET PROCÉDÉ DESTINÉS À LA PRODUCTION D'UN MONOCRISTAL DE CARBURE DE SILICIUM

Publication

EP 2420598 A4 20130501 (EN)

Application

EP 10764335 A 20100319

Priority

- JP 2010054860 W 20100319
- JP 2009100295 A 20090416

Abstract (en)

[origin: EP2420598A1] Disclosed is an apparatus (1) for manufacturing a silicon carbide single crystal, which comprises: a crucible main body (11) that is opened at the top and holds a sublimation material (50) in the bottom portion (11a); a cover member (12) which covers the upper opening (11b) of the crucible main body (11); and a cylindrical guide member (70) which is provided in the crucible main body (11) for guiding the growth of the silicon carbide single crystal when the silicon carbide single crystal is grown from a seed crystal (60). The guide member (70) is separably configured of a first divided body and a second divided body.

IPC 8 full level

C30B 29/36 (2006.01); **C30B 23/00** (2006.01)

CPC (source: EP US)

C30B 23/005 (2013.01 - EP US); **C30B 29/36** (2013.01 - EP US)

Citation (search report)

- [X1] JP 2000219595 A 20000808 - SHIKUSUON KK
- [AD] JP 2004224663 A 20040812 - NAT INST OF ADV IND & TECHNOL
- [A] US 2005028725 A1 20050210 - KATO TOMOHISA [JP], et al
- See references of WO 2010119749A1

Cited by

CN112899782A; EP3889324A1; CN113458905A; US11795576B2

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